

**IN THE CLAIMS:**

**Please amend the claims so as to read as follows:**

1. (Currently amended) A plasma processing method using a process gas supplied into a process chamber to generate plasma from the process gas and process a substrate placed in said process chamber by means of the plasma, wherein

said substrate includes stacked films of at least two types to be etched by the plasma, and, ~~according to any of said films that is to be etched, a change is made in said process gas in a plasma generation period without extinction/regeneration of the plasma, and~~

~~wherein, when said substrate is etched by the plasma in the a~~ plasma generation period, and a change is made in a bias voltage applied to said substrate, together with the change made in said process gas plasma generating condition according to any of said films that are to be etched, said plasma generating condition for stably maintaining generation of the plasma is first changed and thereafter a change is made in said process gas.

2. Cancelled, without prejudice.
3. Cancelled, without prejudice.
4. Cancelled, without prejudice.

5. (Currently Amended) The plasma processing method according to claim 3 1, wherein  
said plasma generating condition for stably maintaining generation of the plasma is pressure of the process gas within said process chamber.
6. (Currently Amended) The plasma processing method according to claim 3 1, wherein  
said plasma generating condition for stably maintaining generation of the plasma is output of a plasma exciting power source.
7. (Currently amended) A plasma processing method using a process gas supplied into a process chamber to generate plasma from the process gas and process a substrate placed in said process chamber by means of the plasma, wherein  
said substrate includes stacked films of at least one Ti-based film and at least one film other than a Al-based film to be etched by the plasma, and,  
~~according to any of said films that is to be etched, a change is made in said process gas in a plasma generation period without extinction/regeneration of the plasma, and~~

~~wherein, in the plasma generation period, a change is made~~  
~~in a bias voltage applied to said substrate, together~~  
~~with the change made in said process gas~~  
when the substrate is etched by the plasma in a plasma  
generation period and a change is made in plasma  
generating condition according to any of the films  
that are to be etched, a plasma generating condition  
for stably maintaining the plasma is first changed,  
and thereafter a change is made in said process gas.

8. (Previously presented) The plasma processing method according to claim 7,  
wherein at least one film other than an Al-based film is an Ti-based film.
9. (Previously presented) The plasma processing method according to claim 7, wherein the process gas includes a mixture of Cl<sub>2</sub> and Ar.
10. (Cancelled)
11. (Cancelled)
12. (Cancelled)
13. (Cancelled)
14. (Cancelled)

15. (Previously Presented) A plasma processing method comprising the steps of:

placing in a process chamber a substrate to be processed that has stacked films;

performing first etching with plasma on said stacked films by supplying a first process gas into said process chamber; completing said first etching without extinguishing said plasma; and

performing second etching with plasma on said stacked films by supplying a second process gas different from said first process gas into said process chamber, wherein

said plasma is maintained without being extinguished until said second etching is started when the substrate is etched by said first etching and said second etching in a plasma generation period a change is made in plasma generating condition such that a plasma generating condition for stably maintaining generation of the plasma is first changed and thereafter the process gas is changed from said first process gas to said second process gas.

16. (Previously presented) A method of manufacturing a semiconductor device by the plasma processing method according to claim 15, wherein said substrate to be processed is a semiconductor substrate and said stacked films of said semiconductor substrate are etched by said plasma processing method.

17. (Previously presented) A method of manufacturing a liquid-crystal display device by the plasma processing method according to claim 15, wherein said substrate to be processed is a substrate of the liquid-crystal display device and said stacked films of said substrate of the liquid-crystal display device are etched by said plasma processing method.

**Please add new Claims 18 and 19 as follows:**

18. (New Claim) The plasma processing method according to Claim 1, wherein  
in the plasma generation period, a change is made in a bias  
voltage applied to said substrate, together with the change  
made in said process gas.
  
19. (New Claim) The plasma processing method according to Claim 7, wherein  
in the plasma generation period, a change is made in a bias  
voltage applied to said substrate, together with the change  
made in said process gas.